

HIGH-SPEED 3.3V 16K x 8 DUAL-PORT STATIC RAM

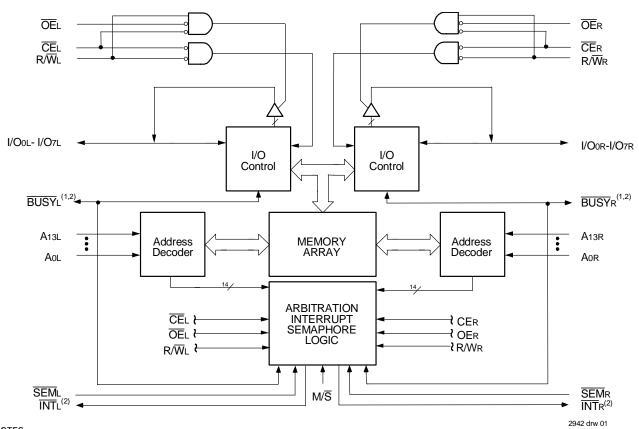
Features

- True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- High-speed access
 - Commercial: 15/20/25/35/55ns (max.)

Functional Block Diagram

- Industrial: 20/25ns (max.)
- Low-power operation
- IDT70V06S
 - Active: 400mW (typ.) Standby: 3.3mW (typ.)
- IDT70V06L
- Active: 380mW (typ.) Standby: 660µW (typ.)
- IDT70V06 easily expands data bus width to 16 bits or more using the Master/Slave select when cascading more than one device

- M/S = VIH for BUSY output flag on Master M/S = VIL for BUSY input on Slave
- Interrupt Flag
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- Battery backup operation—2V data retention
- TTL-compatible, single 3.3V (±0.3V) power supply
- Available in 68-pin PGA and PLCC, and a 64-pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds



NOTES:

1. (MASTER): BUSY is output; (SLAVE): BUSY is input.

OCTOBER 2008

^{2.} BUSY outputs and INT outputs are non-tri-stated push-pull.

Industrial and Commercial Temperature Ranges

41

40

39

38

37

36

35

34

ස 33

õ

29 30 30

A11R

A10R A9R A8R A7R A6R A5R

A12R

Vss

M/S

INTR

A0R

A1R

A2R

A3R

A4R

2942 drw 03

BUSYR

Description

The IDT70V06 is a high-speed 16K x 8 Dual-Port Static RAM. The IDT70V06 is designed to be used as a stand-alone 128K-bit Dual-Port Static RAM or as a combination MASTER/SLAVE Dual-Port Static RAM for 16-bit-or-more word systems. Using the IDT MASTER/ SLAVE Dual-Port Static RAM approach in 16-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control,

11/29/01 RM A13L INDEX 6 5 4 3 2 1 68 67 66 65 64 63 62 61 I/O2L 60 🗆 A5l 10 🗅 A4L I/O3L 59 11 I/O4L 58 □ A3L 12 57 □ A2L 13 Vss 🗆 🗆 A1L 56 14 🗆 Aol 55 15 IDT70V06J 1/07L 🗆 J68-1⁽⁴⁾ 54 16 Vdd 🗌 53 17 68-Pin PLCC 🗆 Vss Vss 🗆 52 18 Top View⁽⁵⁾ I/OOR □ M/S 51 19 **I/O**1R [50 20 1/O2R 49 ⊐ INT_R 21 Vdd [□ Aor 48 22 I/O3r 47 _ A1R 23 I/O4R 46 \Box A2r 24 1/05r [25 45 ⊒ Азк □ A4r I/O6R 44 26 38 39 40 41 2942 drw 02 Атr A6R A5R 11/29/01 OEL RWL SEML SEML CEL A13L VDD A13L A11L A11L A10L A9L INDEX 63 61 60 59 57 55 55 55 53 53 53 57 50 64 49 48 A4L I/O2L I/O3L 2 A3I 47 3 I/O4I 46 A21 I/O5L 4 45 A1L 5 Vss 44 AOL 70V06PF I/O6L 6 43 ĪNTL PN-64⁽⁴⁾ I/O7L BUSYL 7 42

Pin Configurations^(1,2,3)

NOTES:

- 1. All VDD pins must be connected to power supply.
- All Vss pins must be connected to ground supply.
 J68-1 package body is approximately .95 in x .95 in x .17 in
- PN-64 package body is approximately 14mm x 14mm x 1.4mm. 4. This package code is used to reference the package diagram.
- This text does not indicate orientation of the actual part marking.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 400mW of power.

The IDT70V06 is packaged in a ceramic 68-pin PGA and PLCC and a 64-pin thin quad flatpack (TQFP).

Vdd

Vss

I/O0R

I/O1R

I/O2R

I/O3R

I/O4R

I/O5R

Vdd

8

g

10

11

12

13

14

15

16 ~

<u>8</u>

222

R/WR

<u>SEM</u>R

64-Pin TQFP

Top View⁽⁵⁾

23 25 25 26 27

A13R

Vss

CER

Pin Configurations^(1,2,3) (con't.)

01	/03/0)2

Left Port

Vss

 CEL

 R/WL

 OEL

 AOL - A13L

 I/OOL - I/O7L

 SEML

 INTL

 BUSYL

		01/03/0	02										
		11		51 A5L	50 A4L	48 A2L	46 AoL	44 BUSYL	42 M/S	40 INTR	38 A1R	Зб Азк	
		10	53 A7L	52 A6L	49 A3L	47 A1L	45 ĪNTL	43 Vss	41 BUSYR	39 Aor	37 A2R	35 A4R	34 A5R
		09	55 A9L	54 A8L								32 A7R	33 A6R
		08	57 A11L	56 A10L								30 A9R	31 A8R
		07	59 Vdd	58 A12L			10	DT70V				28 A11R	29 A10R
		06	61 N/C	60 A13L				G68-1 8-Pin I op Vie	PGA			26 Vss	27 A12R
		05	63 SEML	62 CEL				24 N/C	25 A13R				
		04	65 OEL	64 R/WL									23 CER
		03	67 I/Ool	66 N/C								20 OER	21 R/WR
		02	68 I/O1L	1 I/O2L	3 I/O4L	5 Vss	7 I/O7L	9 Vss	11 I/O1R	13 Vdd	15 I/O4R	18 I/O7R	19 N/C
	Right Port	01	*	2 Nprog <u>e</u>	4 I/O5L	6 I/O6∟	8 VDD	10 I/Oor	12 I/O2R	14 I/O3R	16 I/O5R	17 I/O6R	
	ĈĒr		Enable	В	С	D	E	F	G	Н	J	ĸ	L
	R/₩r I	REX	d/Write E	nable									2942 drw 04
	ŌĒr	Outp	ut Enable	9									
NOT 1. /	ES: APPDD Allas must be	c Add	reisa to p	ower sup	ply.								
2.	₩ <mark>₩</mark> ₩ss_ pins _must be a	BAS		ound sup	ply.	in				0.65			
3. 4.	r ackage body is appr F S£Ma ckage code is u							Р	'in N	ame	S		
5.	T <u>his t</u> ext does not indica INTR		entation c rupt Flag	of the actu	al part ma	irkin g.							
	BUSY R	Busy	/ Flag										
М	/S	Mast	ter or Sla	ive Selec	ct								
V	DD	Pow	er (3.3V)										

2942 tbl 01

Ground (0V)

3

Industrial and Commercial Temperature Ranges

Truth Table I: Non-Contention Read/Write Control

	Inpu	uts ⁽¹⁾		Outputs				
ĈĒ	R/W	ŌĒ	SEM	I/O0-7	Mode			
Н	Х	Х	Н	High-Z	Deselected: Power-Down			
L		Х	Н	DATAIN	Write to Memory			
L	Н	L	Н	DATAOUT	Read Memory			
Х	Х	Н	Х	High-Z	Outputs Disabled			

NOTE:

1. AOL — A13L \neq AOR — A13R

Truth Table II: Semaphore Read/Write Control⁽¹⁾

	Inp	outs		Outputs					
CE	R/W	ŌĒ	SEM	I/O0-7	Mode				
Н	Н	L	L	DATAOUT	Read Data in Semaphore Flag				
Н	←	Х	L	DATAIN	Write I/Oo into Semaphore Flag				
L	Х	Х	L	_	Not Allowed				

NOTE:

1. There are eight semaphore flags written to via I/Oo and read from I/Oo - I/O7. These eight semaphores are addressed by Ao - A2.

2942 tbl 03

2942 tbl 02

Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Ιουτ	DC Output Current	50	mA

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD + 0.3V.

Capacitance ($TA = +25^{\circ}C$, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Мах.	Unit					
Cin	Input Capacitance	VIN = 3dV	9	рF					
Соит	Output Capacitance	Vout = 3dV	10	рF					
2942 tbl (

NOTES:

 This parameter is determined by device characterization but is not production tested.

3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

2942 tbl 05

NOTE:

2942 tbl 04

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Supply Voltage	3.0	3.3	3.6	۷
Vss	Ground	0	0	0	۷
Vн	Input High Voltage	2.0	_	VDD+0.3 ⁽²⁾	۷
Vil	Input Low Voltage	-0.3 ⁽¹⁾		0.8	۷

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed VDD +0.3V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($V_{DD} = 3.3V \pm 0.3V$)

			70V06S		70V		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	V_{DD} = 3.6V, V_{IN} = 0v to V_{\text{DD}}	-	10	-	5	μA
ILO	Output Leakage Current	Vout = 0V to VDD	_	10		5	μA
Vol	Output Low Voltage	Iol = +4mA		0.4	-	0.4	V
Vон	Output High Voltage	юн = -4mA	2.4	-	2.4	_	V

NOTE:

1. At VDD ≤ 2.0V input leakages are undefined.

2942 tbl 08

2942 tbl 06

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾ ($V_{DD} = 3.3V \pm 0.3V$)

-			Com'l (70V06X15 70V06X20 Com'l Only Com'l & Ind		m'l	70V06X25 Com'l & Ind			
Symbol	Parameter	Test Condition	Versi	on	Тур. ⁽²⁾	Max.	Typ. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Unit
ldd	Dynamic Operating Current (Both Ports Active)	\overline{CE} = VIL, Outputs Disabled SEM = VIH	COM'L	S L	150 140	215 185	140 130	200 175	130 125	190 165	mA
	(BOUT POIS ACUVE)	$f = f_{MAX}^{(3)}$	IND	S L			 130	 195	 125	 180	mA
ISB1	Standby Current (Both Ports - TTL	$ \overline{CE}_{R} = \overline{CE}_{L} = V_{IH} $ $ \overline{SEM}_{R} = \overline{SEM}_{L} = V_{IH} $ $ f = f_{MA} x^{(0)} $	COM'L	S L	25 20	35 30	20 15	30 25	16 13	30 25	mA
	Level Inputs)		IND	S L			15	40	 13	40	mA
ISB2	Standby Current (One Port - TTL	CEL or CER = V⊩ Active_Port Outputs Disabled,	COM'L	S L	85 80	120 110	80 75	110 100	75 72	110 95	mA
	Level Inputs)	f=fMAX ⁽³⁾	IND	S L			75	 115	72	 110	mA
ISB3	Full Standby Current (Both Ports -	Both Ports \overline{CEL} and $\overline{CER} \ge VDD - 0.2V$,	COM'L	S L	1.0 0.2	5 2.5	1.0 0.2	5 2.5	1.0 0.2	5 2.5	mA
	CMOS Level Inputs)	$ \begin{array}{l} V_{IN} \geq V_{DD} - 0.2V \text{ or} \\ V_{IN} \leq 0.2V, f = 0^{(4)} \\ \overline{SEMR} = \overline{SEML} \geq V_{DD} - 0.2V \end{array} $	IND	S L			0.2	5	0.2	5	mA
ISB4	Full Standby Current (One Port -	One Port CEL or CER ≥ VoD - 0.2V	COM'L	S L	85 80	125 105	80 75	115 100	75 70	105 90	mA
	CMOS Level Inputs)	$\label{eq:states} \begin{split} \overline{SEMR} &= \overline{SEML} \ge V \text{DD} - 0.2 V \\ V \text{IN} \ge V \text{DD} - 0.2 V \text{ or } V \text{IN} \le 0.2 V \\ \text{Active Port Outputs Disabled,} \\ f &= f \text{Max}^{(3)} \end{split}$	IND	S L			 75	 115	70	 105	mA

						6X35 Only	70V06X55 Com'l Only		
Symbol	Parameter	Test Condition	Versi	ion	Typ. ^{@)}	Max.	Тур. ⁽²⁾	Max.	Unit
ldd	Dynamic Operating Current (Both Ports Active)	\overline{CE} = VIL, Outputs Disabled SEM = VIH f = fmax ⁽³⁾	COM'L	S L	120 115	180 155	120 115	180 155	mA
	(Buill Funs Active)	I = IMAX*'	IND	S L					mA
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$ \overline{CE}_{R} = \overline{CE}_{L} = VH $ $ \overline{SEM}_{R} = \overline{SEM}_{L} = VH $ $ f = f_{MAX}^{(3)} $	COM'L	S L	13 11	25 20	13 11	25 20	mA
	Level lipus)	I = IMAX*'	IND	S L				mA	
ISB2	Standby Current (One Port - TTL	\overline{CE}_{L} or $\overline{CE}_{R} = V_{H}$ Active Port Outputs Disabled,	COM'L	S L	70 65	100 90	70 65	100 90	mA
	Level Inputs)		IND	S L					mA
ISB3	Full Standby Current (Both Ports -	Both Ports \overline{CE}_{L} and $\overline{CE}_{R} \ge V_{DD} - 0.2V$,	COM'L	S L	1.0 0.2	5 2.5	1.0 0.2	5 2.5	mA
	CMOS Level Inputs) $V_{N} \ge V_{DD} - 0.2V$ or $V_{N} \ge 0.2V$, $f = 0^{(4)}$ SEMR = SEML $\ge V_{DD} - 0.2V$	$\frac{V_{IN} \ge 0.2V, f = 0^{(4)}}{SEM_R} = \overline{SEM}_L \ge V_{DD} - 0.2V$	IND	S L			_		mA
ISB4	Full Standby Current (One Port -	Dne Port - CER > VDD - 0.2V	COM'L	S L	65 60	100 85	65 60	100 85	mA
	CMOS Level Inputs)	$ \begin{array}{l} \overline{SEM_{\mathbb{R}}} = \overline{SEM_{\mathbb{L}}} \geq V \text{DD} - 0.2V \\ \overline{V_{\mathbb{N}}} \geq V \text{DD} - 0.2V \text{ or } V_{\mathbb{N}} \leq 0.2V \\ \text{Active Port Outputs Disabled,} \\ f = f_{\text{MAX}}^{(3)} \end{array} $	IND	S L	_		_		mA

2942 tbl 09b

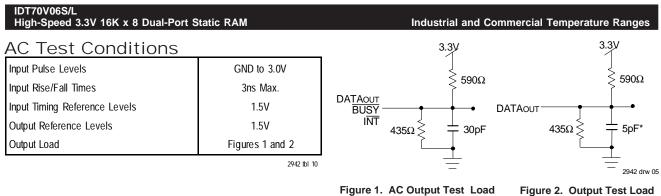
2942 thi 09 a

NOTES: 1. 'X' in part number indicates power rating (S or L)

2. VDD = 3.3, TA = $+25^{\circ}$ C, and are not production tested. Ibb DC = 115mA (Typ.)

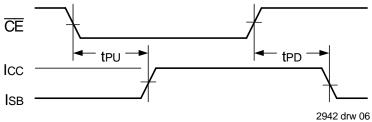
3. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.



(For tLz, tнz, twz, tow) *Including scope and jig.

Timing of Power-Up Power-Down



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

			06X15 I Only	Co	6X20 m'l Ind	70V06X25 Com'l & Ind		
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Min.	Мах.	Unit
READ CYCLE								
trc	Read Cycle Time	15	_	20	-	25	-	ns
taa	Address Access Time	_	15	_	20	-	25	ns
tace	Chip Enable Access Time ⁽³⁾		15		20		25	ns
taoe	Output Enable Access Time ⁽³⁾		10	_	12	_	13	ns
tон	Output Hold from Address Change	3		3	_	3	_	ns
tLz	Output Low-Z Time ⁽¹²⁾	3		3		3	_	ns
tHZ	Output High-Z Time ^(1,2)		10	_	12		15	ns
tPU	Chip Enable to Power Up Time ^(1,2)	0	_	0		0	_	ns
tPD	Chip Disable to Power Down Time ^(1,2)		15		20		25	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10		10		10		ns
t SAA	Semaphore Address Access ⁽³⁾		15		20		25	ns

2942 tbl 11a

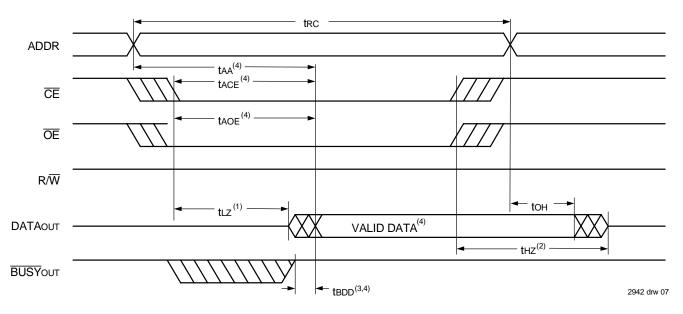
			70V06X35 Com'l Only		70V06X55 Com'l Only	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
READ CYCL	E					
trc	Read Cycle Time	35	_	55		ns
taa	Address Access Time		35		55	ns
İ ACE	Chip Enable Access Time ⁽³⁾		35		55	ns
taoe	Output Enable Access Time ⁽³⁾		20		30	ns
tон	Output Hold from Address Change	3	_	3		ns
tLZ	Output Low-Z Time ^(1,2)	3		3		ns
tHZ	Output High-Z Time ^(1,2)	—	15		25	ns
tPU	Chip Enable to Power Up Time ^(1,2)	0		0		ns
tpd	Chip Disable to Power Down Time ^(1,2)	—	35		50	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	15	_	15		ns
tsaa	Semaphore Address Access ⁽³⁾		35	-	55	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

This parameter is guaranteed but not tested.
 To access SRAM, CE = VIL, SEM = VIH.
 'X' in part number indicates power rating (S or L).

Waveform of Read Cycles⁽⁵⁾



NOTES:

1. Timing depends on which signal is asserted las $\overline{\text{OE}}$ or $\overline{\text{CE}}$.

2. Timing depends on which signal is de-asserted first \overline{CE} or \overline{OE} .

- 3. tbbb delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$

2942 tbl 12a

2942 tbl 12b

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

			06X15 I Only	Co	6X20 m'l Ind	70V06X25 Com'l & Ind			
Symbol	Parameter	Min. Max.		Min.	Мах.	Min.	Мах.	Unit	
WRITE CYCLI	Ē								
twc	Write Cycle Time	15		20		25		ns	
tew	Chip Enable to End-of-Write ⁽³⁾	12	_	15	-	20	_	ns	
taw	Address Valid to End-of-Write	12		15	_	20		ns	
tas	Address Set-up Time ⁽³⁾	0		0	-	0	_	ns	
twp	Write Pulse Width	12	_	15	_	20	_	ns	
twR	Write Recovery Time	0	_	0		0		ns	
tow	Data Valid to End-of-Write	10	_	15	-	15	_	ns	
tHZ	Output High-Z Time ^(1,2)	_	10	-	12	_	15	ns	
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	0	_	ns	
twz	Write Enable to Output in High-Z ^(1,2)	_	10	_	12	_	15	ns	
tow	Output Active from End-of-Write ^(1,2,4)	0		0		0		ns	
tswrd	SEM Flag Write to Read Time	5		5		5	_	ns	
tsps	SEM Flag Contention Window	5		5	_	5		ns	

		70V06X35 Com'l Only Min. Max.		70V06X55 Com'l Only			
Symbol	Parameter			Min.	Мах.	Unit	
WRITE CYCL	E						
twc	Write Cycle Time	35	_	55		ns	
tew	Chip Enable to End-of-Write ⁽³⁾	30	_	45	_	ns	
taw	Address Valid to End-of-Write	30	_	45	_	ns	
tas	Address Set-up Time ⁽³⁾	0		0	_	ns	
twp	Write Pulse Width	25	_	40	_	ns	
twr	Write Recovery Time	0		0	_	ns	
tow	Data Valid to End-of-Write	15		30	_	ns	
tHZ	Output High-Z Time ^(1,2)		15		25	ns	
tdн	Data Hold Time ⁽⁴⁾	0		0	_	ns	
twz	Write Enable to Output in High-Z ^(1,2)	-	15		25	ns	
tow	Output Active from End-of-Write ^(1,2,4)	0		0	_	ns	
tswrd	SEM Flag Write to Read Time	5		5	_	ns	
tsps	SEM Flag Contention Window	5		5	_	ns	

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

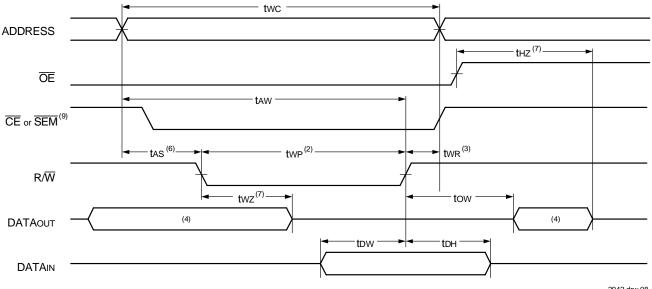
2. This parameter is guaranteed but not tested.

3. To access SRAM, CE = VIL, SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. Either condition must be valid for the entire tew time.

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

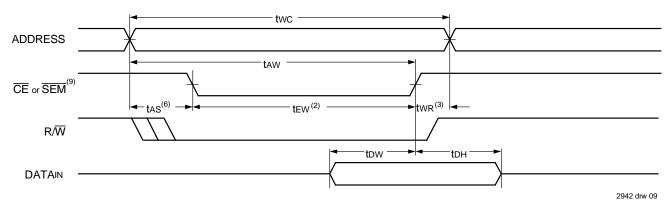
5. 'X' in part number indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,3,5,8)



2942 drw 08

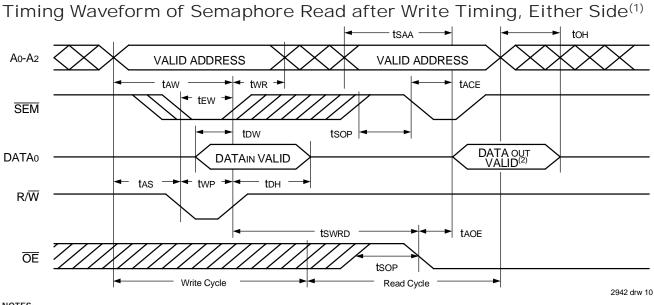
Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,3,5,8)



NOTES:

- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.
- twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle. 3.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W low transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, CE, or R/W.
- Timing depends on which enable signal is de-asserted first, \overline{CE} , or R/\overline{W} . 7
- If \overline{OE} is LOW during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the 8. bus for the required tow. If \overline{OE} is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

9. To access SRAM, CE = VIL and SEM = VIH. To access Semaphore, CE = VIH and SEM = VIL tew must be met for either condition.

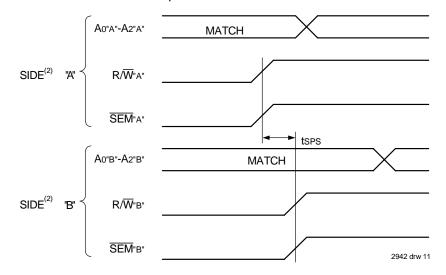


NOTES:

1. $\overline{CE} = V_{IH}$ for the duration of the above timing (both write and read cycle).

2. "DATAOUT VALID" represents all I/O's (I/Oo - I/O7) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



NOTES:

1. DOR = DOL = VIL, $\overline{CE}R = \overline{CE}L = VIH$, Semaphore Flag is released from both sides (reads as ones from both sides) at cycle start.

- 2. "A" may be either left or right port. "B" is the opposite port from "A".
- 3. This parameter is measured from R/\overline{W}_{A^*} or \overline{SEM}_{A^*} going HIGH to R/\overline{W}_{B^*} or \overline{SEM}_{B^*} going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will obtain the flag.

2942 tbl 13b

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

)6X15 'I Ony	Co)6X20 m'l Ind	70V06X25 Com'l & Ind			
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Min.	Max.	Unit	
BUSY TIMINO	G (M/S = VIH)								
tbaa	BUSY Access Time from Address Match	—	15		20		20	ns	
tBDA	BUSY Disable Time from Address Not Matched	—	15		20		20	ns	
tBAC	BUSY Access Time from Chip Enable LOW	_	15		20	_	20	ns	
tBDC	BUSY Disable Time from Chip Enable HIGH	_	15		17	_	17	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		5	_	ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	18		30	_	30	ns	
twн	Write Hold After BUSY ⁽⁵⁾	12	_	15	_	17	_	ns	
BUSY TIMINO	G (M/S = VIL)								
twв	BUSY Input to Write ⁽⁴⁾	0		0		0		ns	
twн	Write Hold After BUSY ⁽⁵⁾	12	_	15		17	_	ns	
PORT-TO-PO	RT DELAY TIMING								
twdd	Write Pulse to Data Delay ⁽¹⁾	_	30		45	_	50	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾	_	25		35		35	ns	

						2942 tbl 13a
			70V06X35 Com'l Only		06X55 I Only	
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Unit
BUSY TIMING	і (М/S = Vін)					
tbaa	BUSY Access Time from Address Match		20		45	ns
tBDA	BUSY Disable Time from Address Not Matched		20		40	ns
tBAC	BUSY Access Time from Chip Enable LOW	_	20	-	40	ns
tBDC	BUSY Disable Time from Chip Enable HIGH	_	20	_	35	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5	-	ns
tbdd	BUSY Disable to Valid Data ⁽³⁾	_	35	-	40	ns
twн	Write Hold After BUSY ⁽⁵⁾	25		25		ns
BUSY TIMING	; (M/S = VIL)					
twв	BUSY Input to Write ⁽⁴⁾	0		0		ns
twн	Write Hold After BUSY ⁽⁵⁾	25		25		ns
PORT-TO-PO	RT DELAY TIMING					
twdd	Write Pulse to Data Delay ⁽¹⁾		60		80	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		45		65	ns

NOTES:

1. Port-to-port delay through SRAM cells from writing port to reading port, refer to "Timing Waveform of Read With BUSY (M/S = VIH) or "Timing Waveform of Write With Port-To-Port Delay (M/S=VIL)".

2. To ensure that the earlier of the two ports wins.

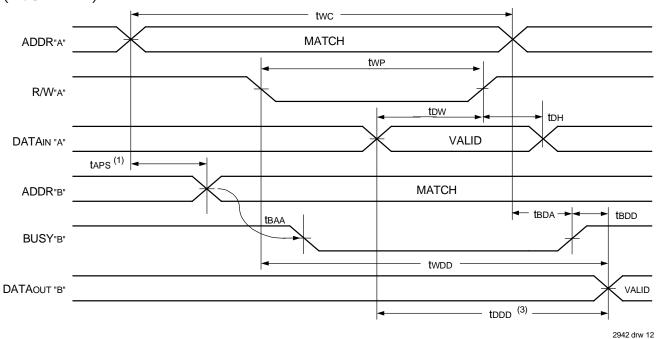
3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual) or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited during contention.

5. To ensure that a write cycle is completed after contention.

6. "X" is part numbers indicates power rating (S or L).

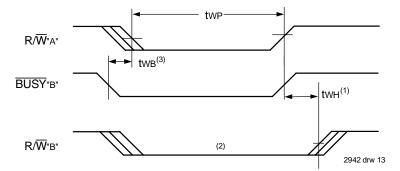
Timing Waveform of Write with Port-To-Port Read and **BUSY**^(2,4,5) $(M/\overline{S} = VIH)$



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = VIL$ (SLAVE).
- $2. \quad \overline{CE}_L = \overline{CE}_R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port. 4. If M/S = V_{IL}(slave) then BUSY is input. Then for this example $\overline{BUSY}_{A^*} = V_{IH}$ and \overline{BUSY}_{B^*} input is shown above.
- 5. All timing is the same for left and right port. Port "A" may be either left or right port. Port "B" is the port opposite from Port "A".

Timing Waveform of Write with **BUSY**



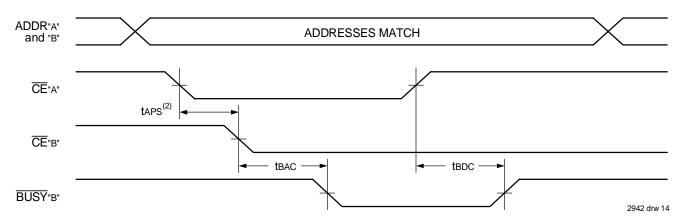
NOTES:

1. twH must be met for both $\overline{\text{BUSY}}$ input (slave) output master.

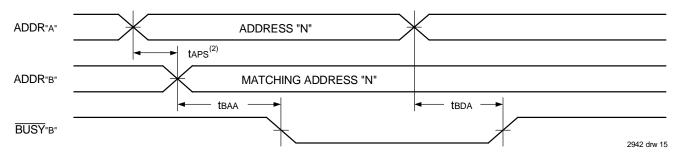
2. BUSY is asserted on Port "B" Blocking R/W B", until BUSY B" goes HIGH.

3. twb is only for the slave version.

Waveform of **BUSY** Arbitration Controlled by \overline{CE} Timing⁽¹⁾ (M/ \overline{S} = VIH)



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing⁽¹⁾ (M/ \mathbf{S} = VIH)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

			06X15 I Only	Co	6X20 m'l Ind	Co)6X25 m'l Ind	
Symbol	Parameter	Min. Max. Min. Max.				Min.	Мах.	Unit
INTERRUPT	TIMING	-	-	-				
tas	Address Set-up Time	0	_	0	_	0		ns
twr	Write Recovery Time	0	_	0	_	0		ns
tiNS	Interrupt Set Time	—	15		20		20	ns
tinr	Interrupt Reset Time		15		20		20	ns

2942 tbl 14a

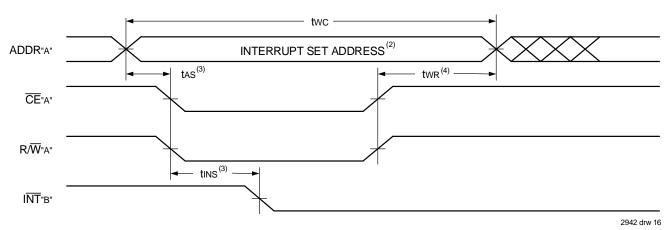
		70V06X35 Com'l Only		70V06X55 Com'l Only			
Symbol	Parameter Min. Max. Min. Ma						
INTERRUPT 1	IMING						
tas	Address Set-up Time	0		0		ns	
twr	Write Recovery Time	0		0		ns	
tiNS	Interrupt Set Time		25	-	40	ns	
tinr	Interrupt Reset Time	-	25		40	ns	

NOTE:

1. 'X' in part number indicates power rating (S or L).

2942 tbl 14b

Waveform of Interrupt Timing⁽¹⁾



NOTES:

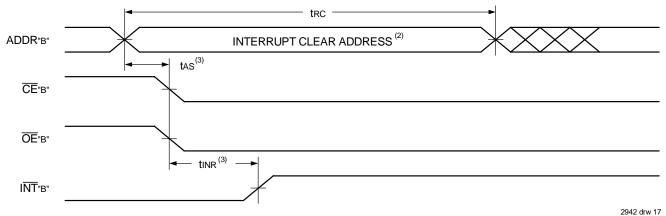
1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

2. See Interrupt Truth Table III.

Timing depends on which enable signal (CE or R(W)) is asserted last.
 Timing depends on which enable signal (CE or R(W)) is de-asserted first.

Industrial and Commercial Temperature Ranges

Waveform of Interrupt Timing⁽¹⁾ (con't.)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

2. See Interrupt Truth Table III.

3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.

Truth Table III — Interrupt Flag⁽¹⁾

		Left Po	rt				Right P			
R/₩L	CE L	OEL	A13L-A0L	ĪNTL	R/Wr	ĊĒr	OE R	A13R-A0R	Ī NT r	Function
L	L	Х	3FFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	3FFE	Х	Set Left INTL Flag
Х	L	L	3FFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INT∟ Flag

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = VIH.$

2. If $\overline{\text{BUSY}}_{L} = \text{ViL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = \text{VIL}$, then no change.

2942 tbl 15

Truth Table IV — Address **BUSY** Arbitration

	In	puts	Out	puts	
Ē	CER	A13L-A0L A13R-A0R	BUS YL ⁽¹⁾	BUSYR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

2942 tbl 16

1. Pins BUSYL and BUSYL AN

2. Lif the inputs to the opposite port were stable prior to the address and enable inputs of this port. Hif the inputs to the opposite port became stable after the address and enable inputs of this port. If the inputs is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs cannot be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Truth Table V — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D7 Left	Do - D7 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V06.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo - I/O7). These eight semaphores are addressed by Ao -A2.

3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT70V06 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V06 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = VIH$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is set when the right port writes to memory location 3FFE

(HEX). The left port clears the interrupt by reading address location 3FFE. Likewise, the right port interrupt flag (\overline{INTR}) is set when the left port writes to memory location 3FFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 3FFF. The message (8 bits) at 3FFE or 3FFF is user-defined. If the interrupt function is not used, address locations 3FFE and 3FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the SRAM have accessed the same location at the same time. It also

2942 tbl 17

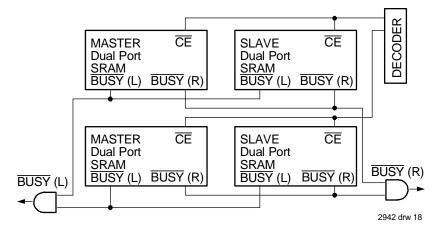


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V06 SRAMs.

allows one of the two accesses to proceed and signals the other side that the SRAM is "busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT 70V06 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the busy indication for the resulting array requires the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V06 SRAM array in width while using BUSY logic, one master part is used to decide which side of the SRAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the BUSY signal as a write inhibit signal. Thus on the IDT70V06 RAM the BUSY pin is an output if the part is used as a master (M/S pin = VIH), and the BUSY pin is an input if the part used as a slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for part of the other word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long

enough for a $\overline{\text{BUSY}}$ flag to be output from the master before the actual write pulse can be initiated with the R/\overline{W} signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V06 is an extremely fast Dual-Port 16K x 8 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port SRAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port SRAM or any other shared resource.

The Dual-Port SRAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port SRAM. These devices have an automatic powerdown feature controlled by CE, the Dual-Port SRAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where CE and SEM are both HIGH.

Systems which can best use the IDT70V06 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V06's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V06 does not use its semaphore flags

Industrial and Commercial Temperature Ranges

to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port SRAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it assumes control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70V06 in a separate memory space from the Dual-Port SRAM. This address space is accessed by placing a LOW input on the SEM pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{OE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

Industrial and Commercial Temperature Ranges

Using Semaphores—Some Examples

Perhaps the simplest application of semaphores is their application as resource markers for the IDT70V06's Dual-Port SRAM. Say the 16K x 8 SRAM was to be divided into two 8K x 8 blocks which were to be dedicated at any one time to servicing either the left orright port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 8K of Dual-Port SRAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 8K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 8K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

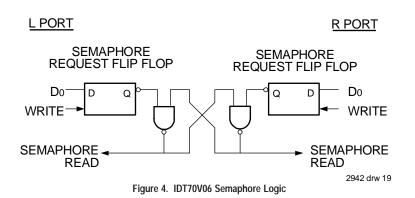
Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 8K blocks of Dual-Port SRAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port SRAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

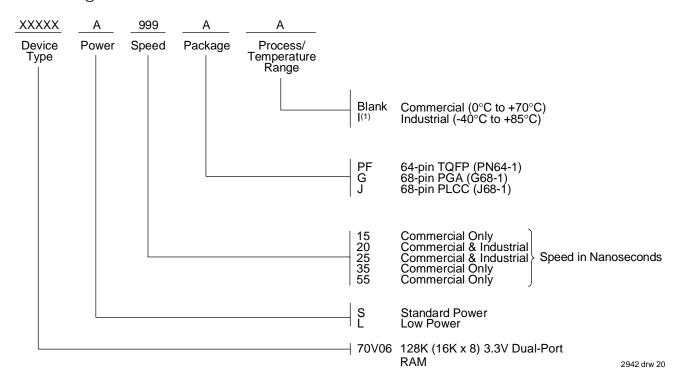
Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned SRAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.



Ordering Information



NOTE:

1. Contact your local sales office for Industrial temp range in other speeds, packages and powers.

Datasheet Document History

3/10/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Page 2 and 3 Added additional notes to pin configurations
6/9/99:	Changed drawing format
11/10/99:	Replaced IDT logo
3/10/00:	Added 15 & 20ns speed grades
	Upgraded DC parameters
	Added Industrial Temperature information
	Changed ±200mV to 0mV
5/30/00:	Page 5 Increased storage temperature parameter
	Clarified TA parameter
	Page 6 DC Electrical parameters-changed wording from "open" to "disabled"

Datasheet Document History (cont'd)

11/20/01: Page 1 Corrected standby power designation from mW to μW

- Page 2 & 3 Added date revision for pin configurations
- Page 2, 3, 5 & 6 Changed naming conventions from Vcc to Vbb and from GND to Vss
- Page 6 Removed Industrial temp for standard power for 20ns and 25ns speeds from DC Electrical Characteristics Removed Industrial temp for 35ns and 55ns speeds from DC Electrical Characteristics
- Pages 8,13 & 16 Removed Industrial temp for 35ns and 55ns speeds from AC Electrical Characteristics
- Page 8 Replaced table 11 with table 11a to show AC Electrical Characteristics for READ CYCLE for 15, 20 & 25ns
- Page 22 Removed Industrial temp from 35ns and 55ns in ordering information

Page 22 Removed "IDT" from orderable part numbe 10/23/08:



CORPORATE HEADQUARTERS 6024 Silver Creek Valley Road San Jose, CA 95138

for SALES: 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com

for Tech Support: 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.